

**ABSTRACT OF THE DISCLOSURE**

1       A semiconductor device including memory cells isolated by a trench that may be self  
2       aligned with a stacked film pattern (7) has been disclosed. The memory cells may be flash  
3       memory cells having an active gate film (2) that may be thinner than a gate oxide film (30).  
4       The active gate film (2) may be located in a central portion under of a gate electrode (3). The  
5       gate oxide film (30) may be located under end portions of the gate electrode (3). In this way,  
6       a distance between a shoulder portion of a trench (11) and a gate electrode (3) may be  
7       increased. Thus, an electric field concentration in the shoulder portion of the trench (11) may  
8       be decreased and memory cell characteristics may be improved.